


General Description

The AO4485/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ with low gate charge. This device is suitable for use as a DC-DC converter application.

AO4485 and AO4485L are electrically identical.

-RoHS Compliant

-AO4485L is Halogen Free

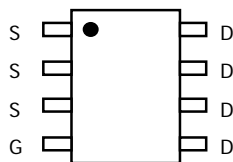
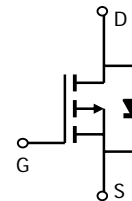
Features

V_{DS} (V) = -40V

I_D = -10A (V_{GS} = -10V)

$R_{DS(ON)}$ < 15m Ω (V_{GS} = -10V)

$R_{DS(ON)}$ < 20m Ω (V_{GS} = -4.5V)


SOIC-8

Absolute Maximum Ratings $T_J=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	10 Sec	Steady State	Units	
Drain-Source Voltage	V_{DS}	-40		V	
Gate-Source Voltage	V_{GS}	± 20		V	
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	-12	-10	A
		$T_A=70^\circ\text{C}$	-9	-8	
Pulsed Drain Current ^B	I_{DM}	-120			
Avalanche Current ^G	I_{AR}	-28			
Repetitive avalanche energy $L=0.3\text{mH}$ ^G	E_{AR}	118		mJ	
Power Dissipation ^A	P_D	$T_A=25^\circ\text{C}$	3.1	1.7	W
		$T_A=70^\circ\text{C}$	2.0	1.1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$	

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
$t \leq 10\text{s}$				
Maximum Junction-to-Ambient ^A	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$
Steady State				
Maximum Junction-to-Lead ^C				

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -40\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.7	-1.9	-2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS} = -10\text{V}, V_{DS} = -5\text{V}$	-120			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{V}, I_D = -10\text{A}$ $T_J = 125^\circ\text{C}$ $V_{GS} = -4.5\text{V}, I_D = -8\text{A}$		12.5 19 16	15 23 20	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -10\text{A}$		25		S
V_{SD}	Diode Forward Voltage	$I_S = -1\text{A}, V_{GS} = 0\text{V}$		-0.7	-1	V
I_S	Maximum Body-Diode Continuous Current				-3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-20\text{V}, f=1\text{MHz}$		2500	3000	pF
C_{oss}	Output Capacitance			260		pF
C_{rss}	Reverse Transfer Capacitance			180		pF
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	2.5	4	6	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-20\text{V}, I_D=-10\text{A}$		42	55	nC
$Q_g(4.5\text{V})$	Total Gate Charge			18.6		nC
Q_{gs}	Gate Source Charge			7		nC
Q_{gd}	Gate Drain Charge			8.6		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-20\text{V},$ $R_L = 2\Omega, R_{GEN}=3\Omega$		9.4		ns
t_r	Turn-On Rise Time			20		ns
$t_{D(off)}$	Turn-Off Delay Time			55		ns
t_f	Turn-Off Fall Time			30		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-10\text{A}, di/dt=100\text{A}/\mu\text{s}$		38	49	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-10\text{A}, di/dt=100\text{A}/\mu\text{s}$		47		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $t \leq 300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

G: E_{AR} and I_{AR} ratings are based on low frequency and duty cycles to keep $T_J=25^\circ\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

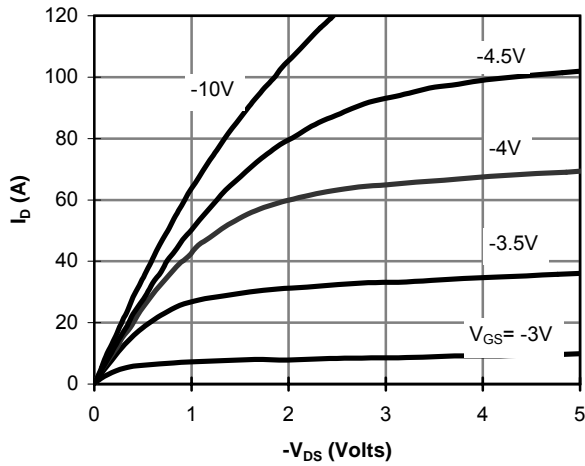


Figure 1: On-Region Characteristics

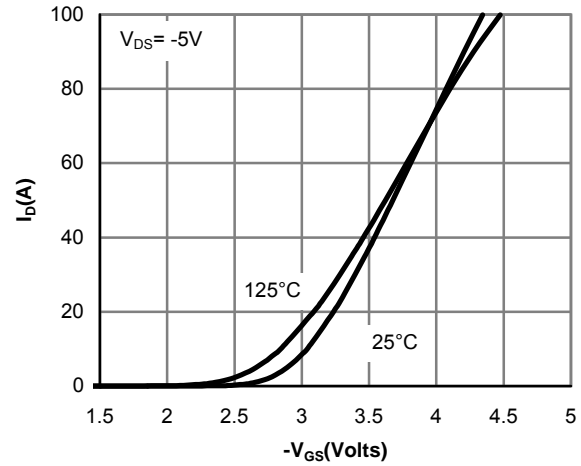


Figure 2: Transfer Characteristics

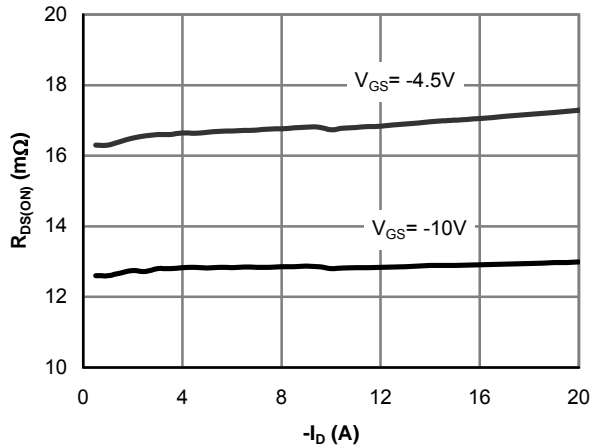


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

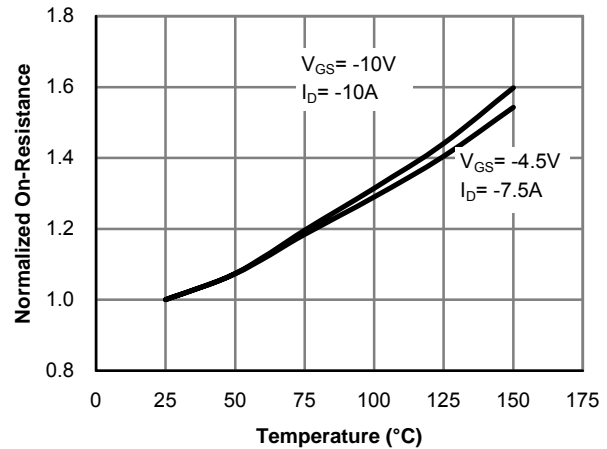


Figure 4: On-Resistance vs. Junction Temperature

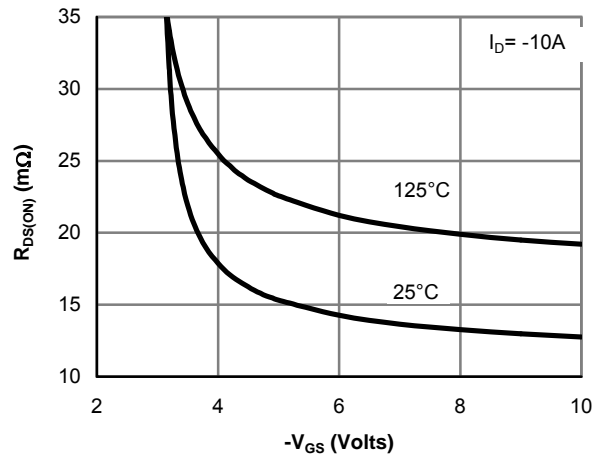


Figure 5: On-Resistance vs. Gate-Source Voltage

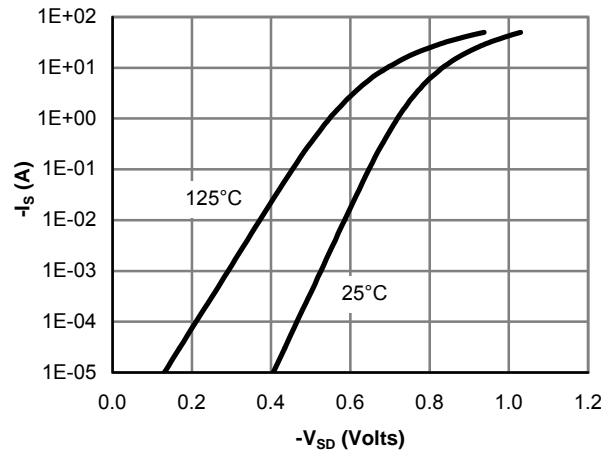


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

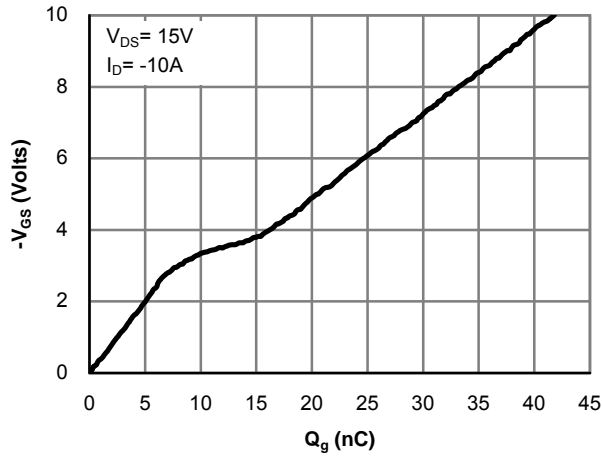


Figure 7: Gate-Charge Characteristics

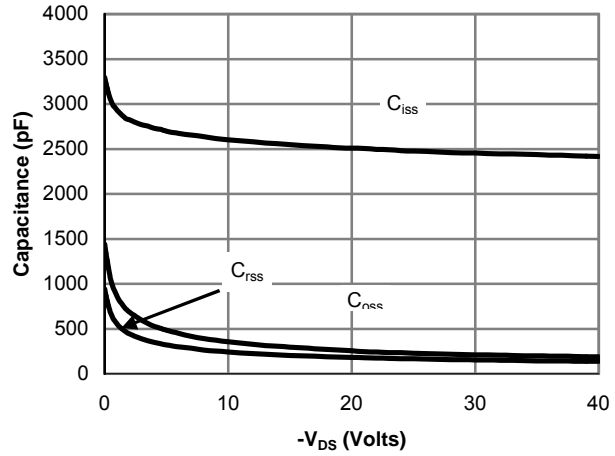


Figure 8: Capacitance Characteristics

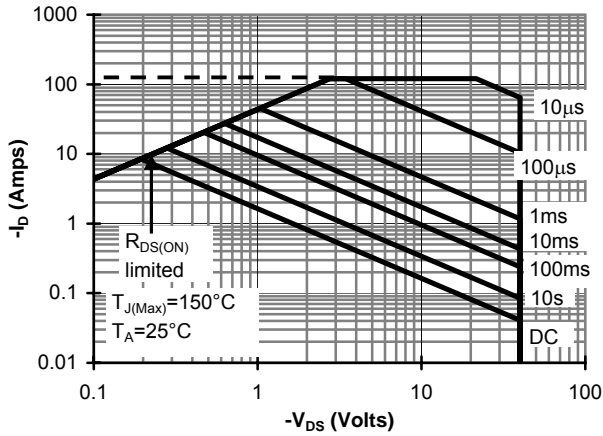


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

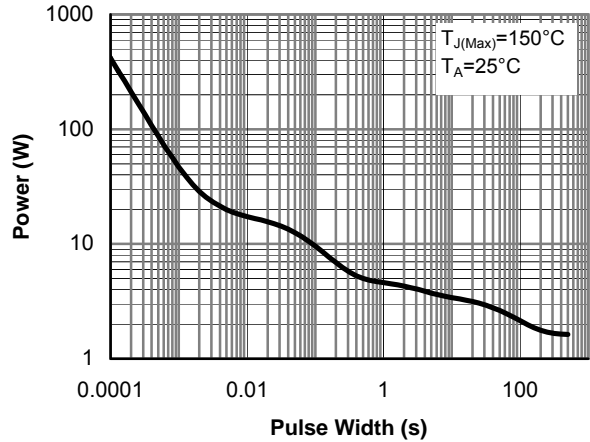


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

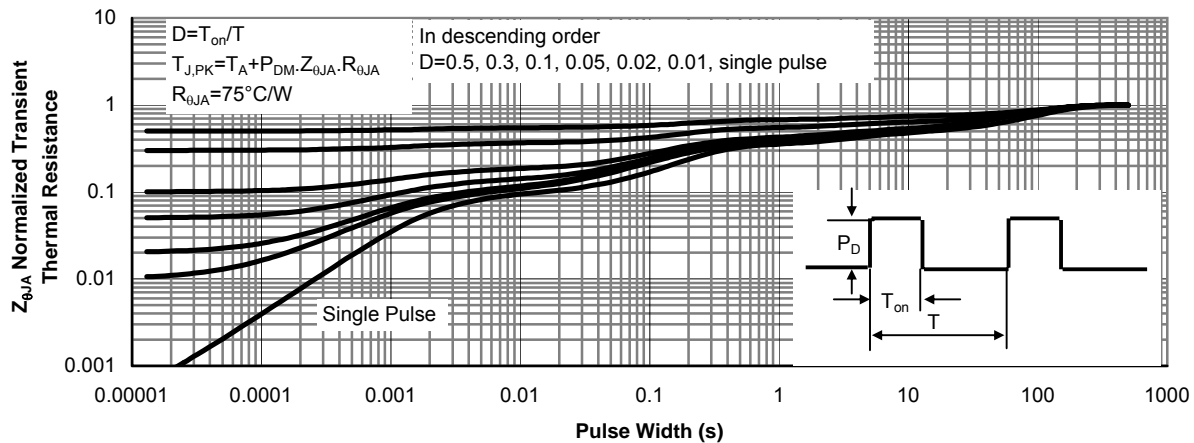


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)